

FILE 'USPAT' ENTERED AT 17:07:33 ON 15 JUN 1999

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*       U . S .   P A T E N T   T E X T   F I L E       *
*
*   THE WEEKLY PATENT TEXT AND IMAGE DATA IS CURRENT    *
*   THROUGH June 15,1999.                                *
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=> s amorphous(w)silicon(w)carbide(4w)gate

66285 AMORPHOUS

204090 SILICON

65346 CARBIDE

218161 GATE

L5 . 1 AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

=> d his

(FILE 'USPAT' ENTERED AT 17:02:27 ON 15 JUN 1999)
L1 1 S AMORPHOUS (W) SILICON (W) CARBIDE (2W) GATE

FILE 'JPO' ENTERED AT 17:06:55 ON 15 JUN 1999
L2 0 S AMORPHOUS (W) SILICON (W) CARBIDE (2W) GATE
L3 0 S AMORPHOUS (W) SILICON (W) CARBIDE (3W) GATE
L4 0 S AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

FILE 'USPAT' ENTERED AT 17:07:33 ON 15 JUN 1999
L5 1 S AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

=> d cit 1-

1. 4,849,797, Jul. 18, 1989, Thin film transistor; Yasuhiro Ukai, et al., 257/57, 77 [IMAGE AVAILABLE]